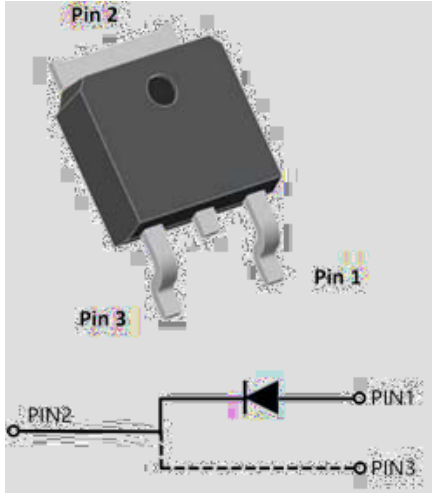


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I_F 135°C	16A
Q_C	53nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-252

Terminals: Tin plated leads

Polarity: As marked

Maximum Ratings ($T_c=25$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112010DQG2
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	V_{RRM}	V	1200
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	V_{RSM}	V	1200
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	V_{DC}	V	1200
Continuous forward current @ $T_c=25^\circ\text{C}$	I_F	A	33
Continuous forward current @ $T_c=135^\circ\text{C}$			16
Continuous forward current @ $T_c=159^\circ\text{C}$			10
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	I_{FSM}	A	85
Power Dissipation @ $T_c=25^\circ\text{C}$	P_{TOT}	W	189
Power Dissipation @ $T_c=110^\circ\text{C}$			82
i^2t Value @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	i^2dt	A^2S	36
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175



YJD112010DQG2

Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	V_F	V	$I_F=10A, T_j=25^{\circ}C$	1.42	1.54
			$I_F=10A, T_j=175^{\circ}C$	2.1	-
Reverse leakage current	I_R	μA	$V_R=1200V, T_j=25^{\circ}C$	1.3	13
			$V_R=1200V, T_j=175^{\circ}C$	6	-
Total capacitive charge	Q_C	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{V_R} I_C(V)dV$	53	-
Total capacitance	C	μF	$V_R=0V, f=1MHZ$	700	-
			$V_R=400V, f=1MHZ$	49	-
			$V_R=800V, f=1MHZ$	39	-
Capacitance Stored Energy	E_C	μJ	$V_R=800V$	14	-

Thermal Characteristics $T_a=25$ Unless otherwise specified

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R_{J-C}	$^{\circ}C/W$	0.79

Typical Characteristics

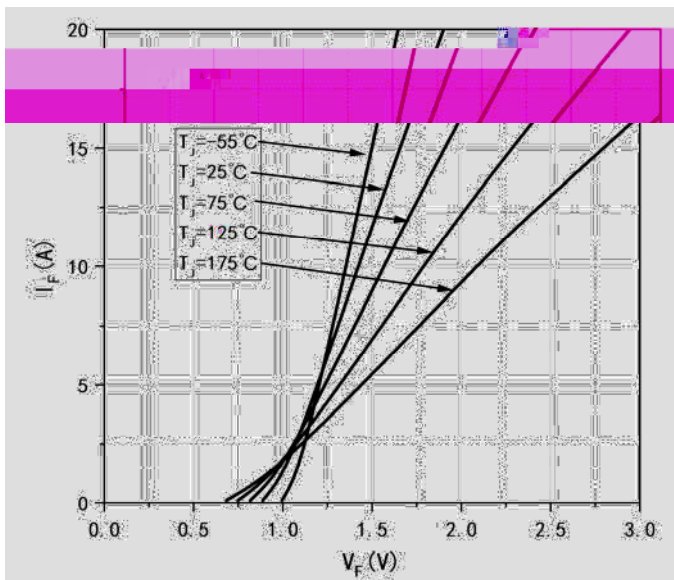


Figure 1. Forward Characteristics

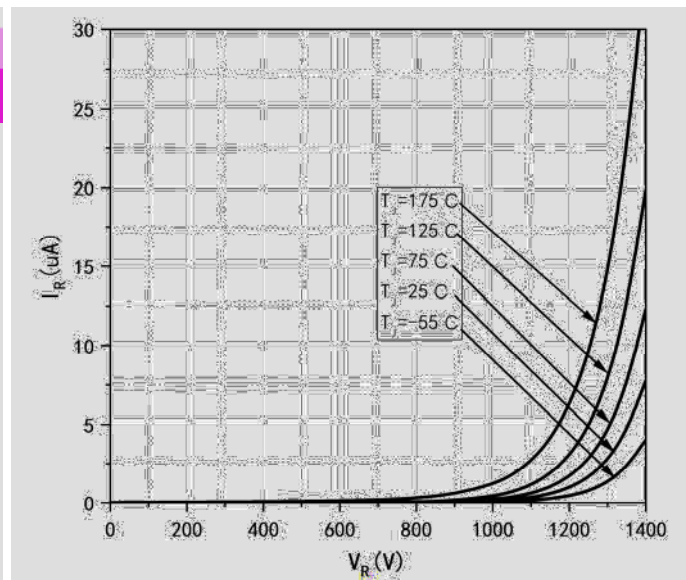


Figure 2. Reverse Characteristic

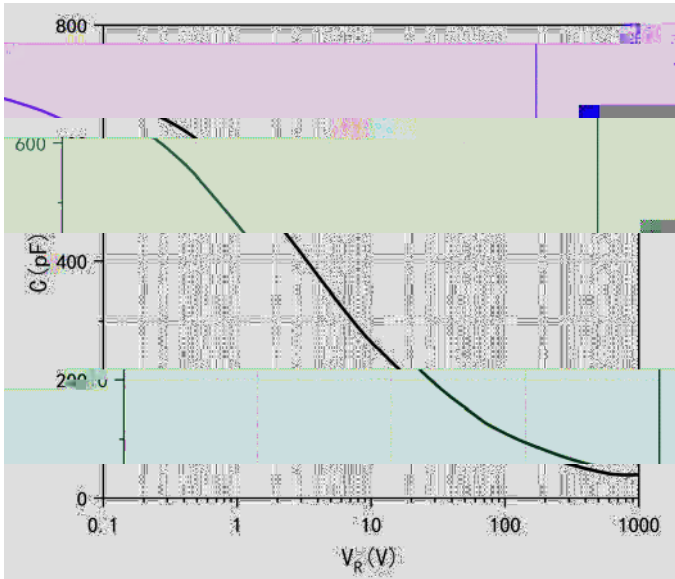


Figure 3. Capacitance vs. Reverse Voltage

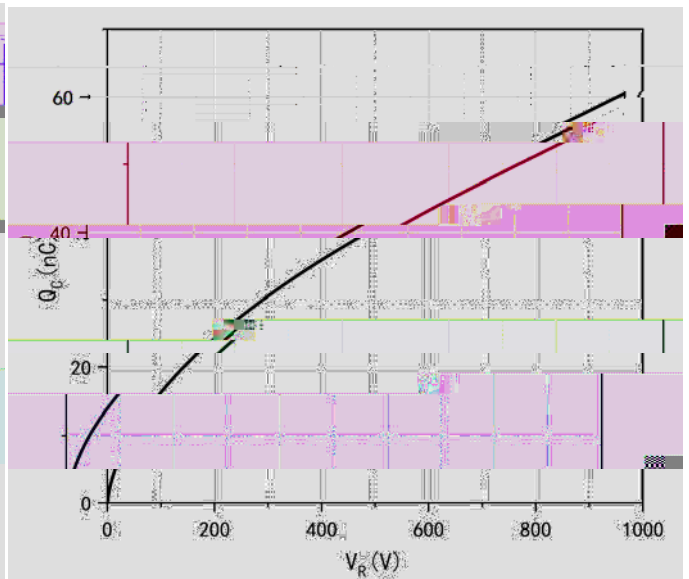


Figure 4. Total Capacitance Charge vs. Reverse Voltage

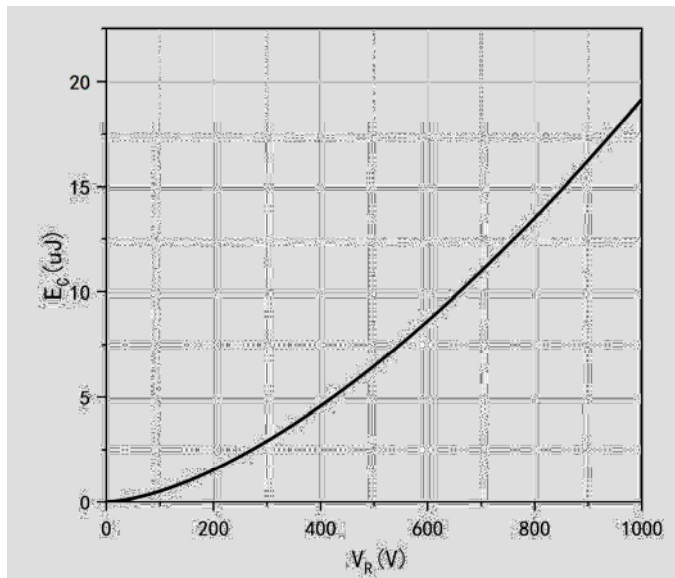


Figure 5. Capacitance Stored Energy

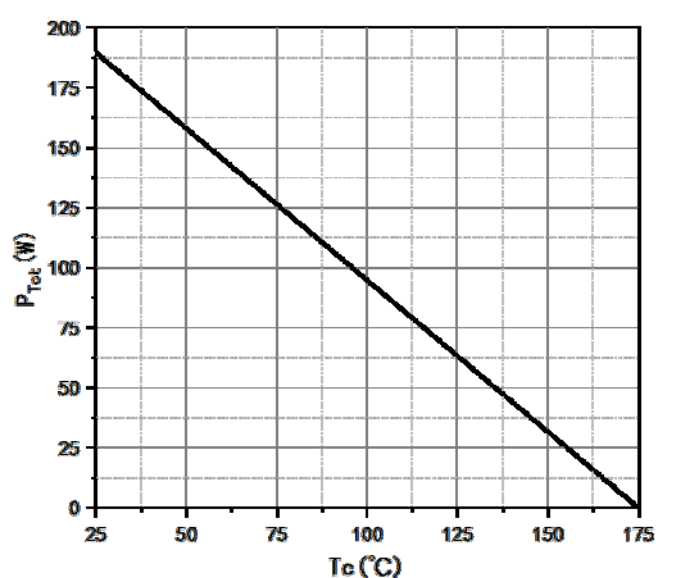


Figure 6. Power Derating

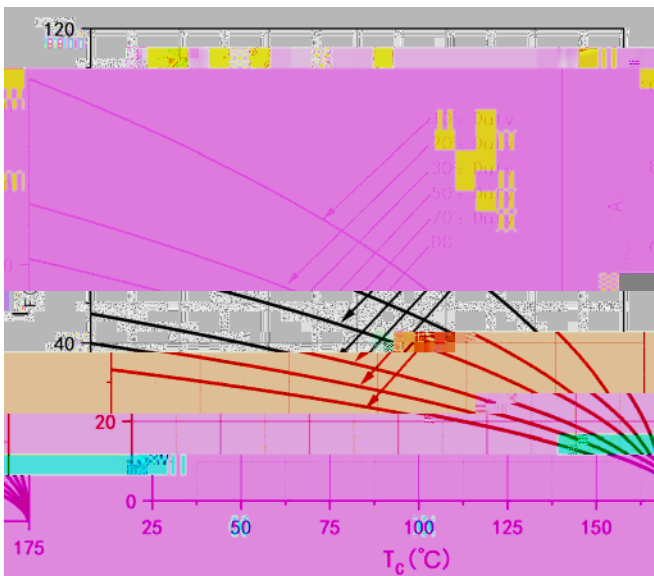


Figure 7. Current Derating

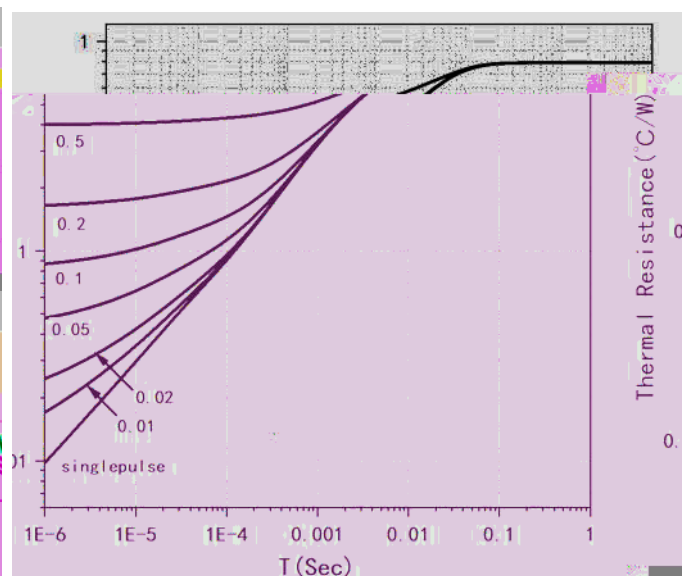
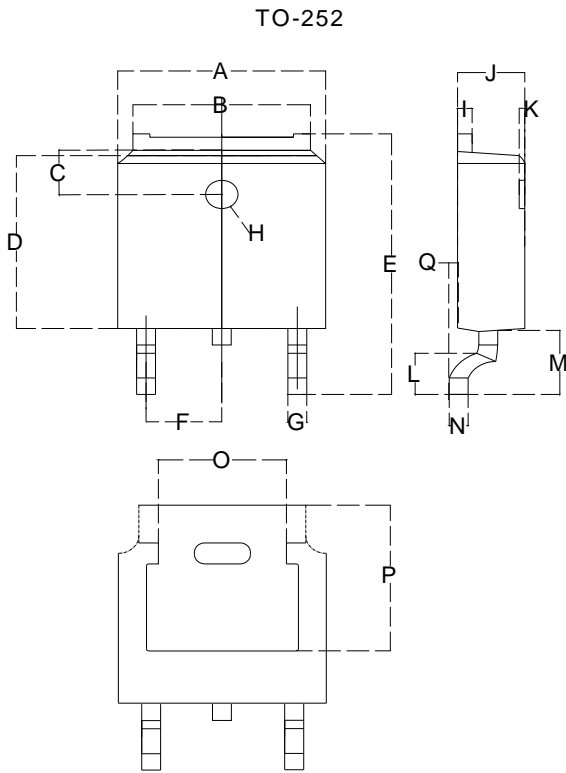


Figure 8. Transient Thermal Impedance



YJD112010DQG2

Outline Dimensions



Dimensions in millimeters

TO-252		
Dim	Min	Max
A	6.500	6.700
B	5.100	5.460
C	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
H	1.050	1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.730	3.080
N	0.430	0.580
O	4.20	4.95
P	5.15	5.45
Q	0	0.2



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